

**RGO Technical Note 117
CCD Camera EEV #12**

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1. General Description.

CCD Device Number A5500-5

CCD Device Type EEV4280. Thinned and AR Coated.

13.5 μ m pixels. 2148 x 4128 Pixels total. 50 x-underscan, 50 x-overscan, 28 y-overscan.

Two working amplifiers, 4 and 5 electrons RMS noise.

Cosmetically clean with 1 bright column only.

QE=65% at 380nm, 81% at 400nm, 80% at 650nm, 14% at 950nm.

Dark current= 0.75e/hour at -120C.

Full Well= 240,000 electrons

2. Operational Modes.

The EEV42-80 devices have an on-chip gain switch that can reduce output node sensitivity by a factor of approximately 2.8. The default state is hi-sensitivity mode which minimises readout noise and gives an output sensitivity of about 4.5 μ V / electron. This mode is recommended for spectroscopic applications. Lo-sensitivity mode can be selected at the CCD engineering terminal (see below) and allows the full dynamic range of the CCD to be utilised. In this mode, which is recommended for prime focus imaging, the CCD full-well signal matches closely the input range of the ADC. Readout noise rises to approximately 10e RMS but in most direct imaging applications this will be insignificant next to sky noise.

To select Hi-Gain Mode (default) type : **'hopg'**

To select Lo-Gain Mode (default) type : **'lopg'**

To read back Mode setting type : **'see'**

An Anti-Blooming (AB) operational mode is also implemented for this camera although the default state has it switched off. When enabled (see below) the vertical clock phases 1 and 2 are modulated so that the integrated charge in each pixel is 'wobbled' back and forth. Excess charge that would otherwise produce a bloomed feature is removed by this process, which is thought to involve the injection of holes from the CCD channel stops. Each 'wobble' cycle can remove >200 electrons. The wobble frequency used for this device was 330 Hz. The drawback of AB clocks is that a large number (>4500) of bright spot features are generated in the image. One very bright saturated LED type defect is also created close to the left hand amplifier. Due to these drawbacks, the use of AB mode is not really recommended for scientific imaging.

To switch AB clocks on type at the engineering terminal : **1 VHT 'ANTI-BLOOM C!'**

To switch off : **0 VHT 'ANTI-BLOOM C!'**

To check present setting : **VHT 'ANTI-BLOOM C?'**

3. Image Quality.

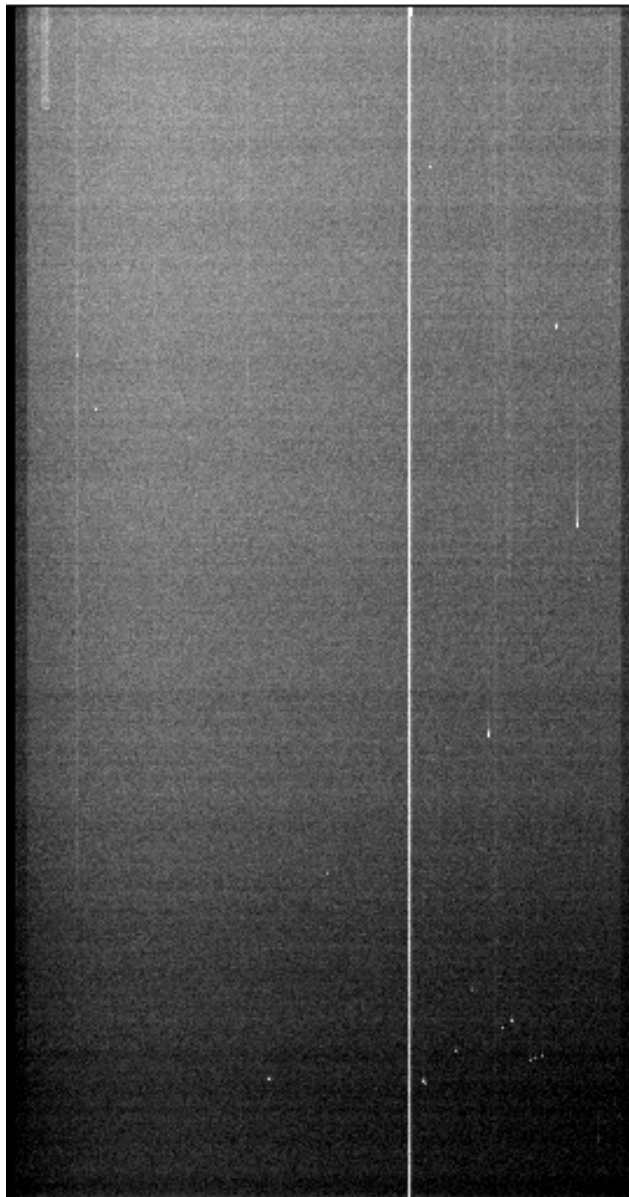
Image quality was assessed from a series of five 600s dark frames. These were combined into one image using the IRAF 'imcombine' function with parameter 'reject' set equal to 'minmax' in order to reject cosmic ray features. Bright columns were then located by manual inspection of the resultant image. The IRAF functions 'daofind' and 'daophot' were then used to log isolated 'hot' pixels. The locations of the defects recorded in this section have co-ordinates referenced to the left hand CCD amplifier.

Measurement temperature was -120C.

3.1. Defective Columns.

A bright feature near the top right of the image spills charge down column 1376. A trap cluster just visible on the top left of the image blocks all signal that is vertically transferred through it.

600 second dark frame



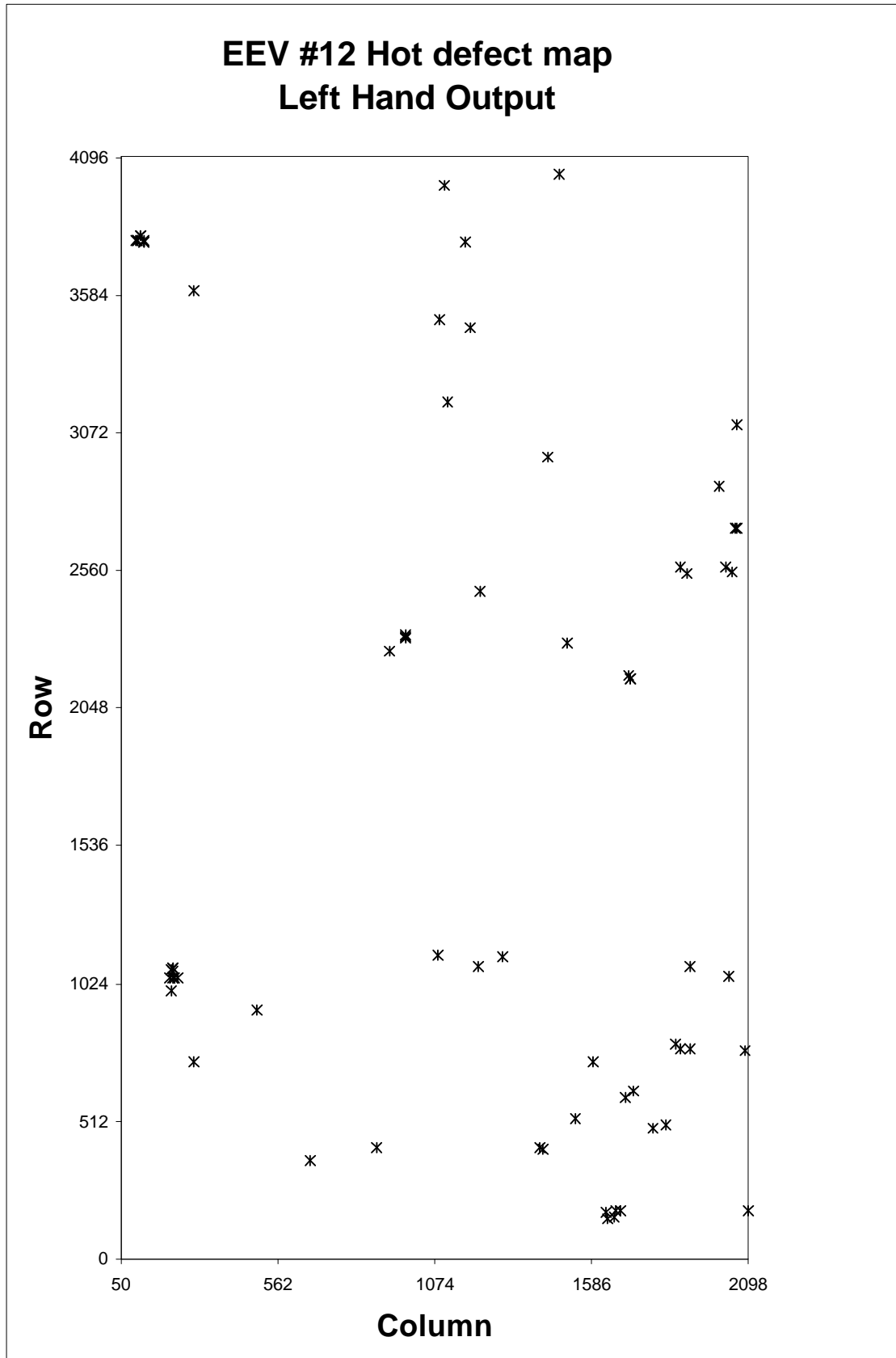
3.2. Hot Spots.

The size and location, referenced to the left hand CCD amplifier, of significant hot spots is tabulated below and shown graphically on the following page.

X-Coord	Y-Coord	electrons after 600s	electrons after 300s
1640	150	612	345
1660	158	232	133
1633	172	122	56
2098	178	195	128
1665	180	4605	2296
1679	180	376	128
668	366	288	182
1428	407	248	186
1418	416	455	67
884	417	179	460
1788	486	142	238
1827	501	217	142
1535	522	169	237
1695	602	205	210
1723	628	332	374
286	735	74	0
1591	736	186	234
2089	778	103	43
1878	779	145	102
1907	779	1110	465
1860	798	211	116
495	926	931	434
211	999	1022	445
211	1043	162	62
219	1047	180	92
226	1047	628	334
233	1047	450	252
2035	1052	292	197
219	1073	4672	2283
214	1077	141	111
217	1084	2221	1112
220	1083	4474	2240
1216	1088	319	118
1910	1091	184	112
1296	1126	185	160
1087	1131	200	205
1710	2161	245	173
1715	2161	1525	809
1707	2172	2802	1423
927	2262	691	349
1507	2292	261	286
979	2310	943	465
979	2317	465	174

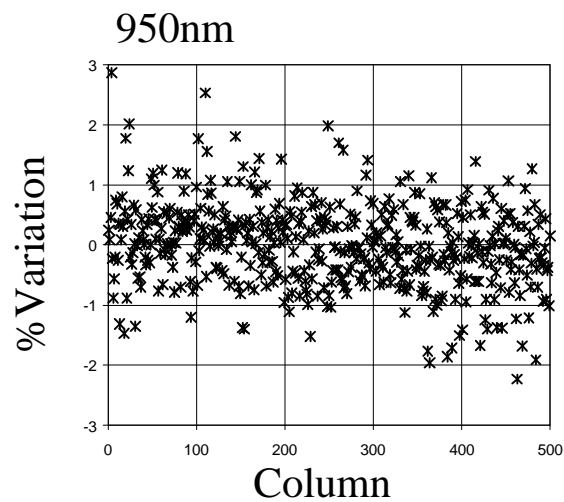
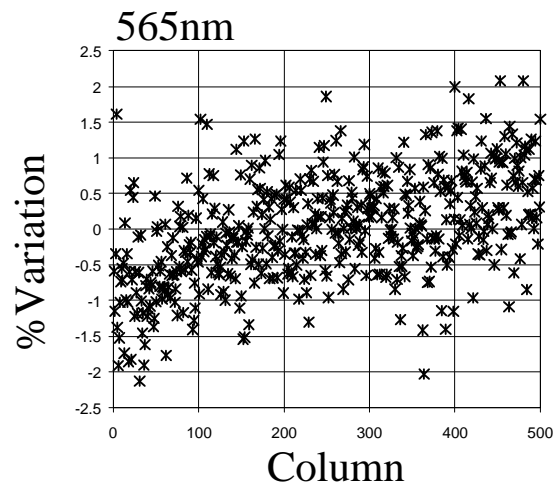
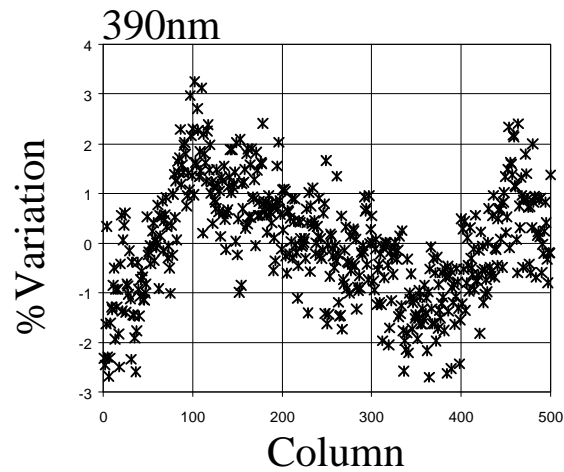
X-Coord	Y-Coord	electrons after 600s	electrons after 300s
979	2321	84	41
1222	2481	171	86
1897	2548	125	130
2043	2553	80	25
1876	2570	150	103
2023	2570	90	20
2057	2715	667	342
2060	2715	512	234
2003	2872	207	129
1441	2979	806	417
2062	3100	23273	11521
1116	3186	22	38
1190	3465	409	182
1088	3495	60	48
290	3604	368	171
122	3779	23726	11871
123	3779	21432	10739
1177	3782	97	49
102	3785	3097	1482
100	3788	9204	4660
104	3788	4838	2291
123	3788	1672	835
113	3804	2506	1156
116	3804	2654	1224
1107	3992	919	427
1482	4031	3607	1718
1376	3811	>240000	>240000

In addition to these hot spots, a sea level cosmic ray flux of 1940 events per hour was measured (2.2 events cm⁻² min⁻¹).



3.3. Pixel Response Non-Uniformity (PRNU).

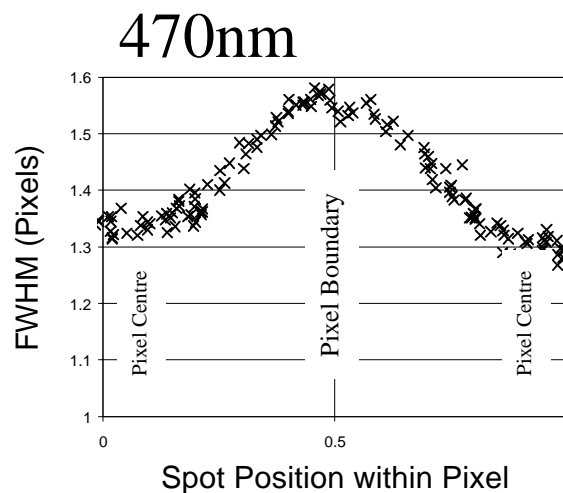
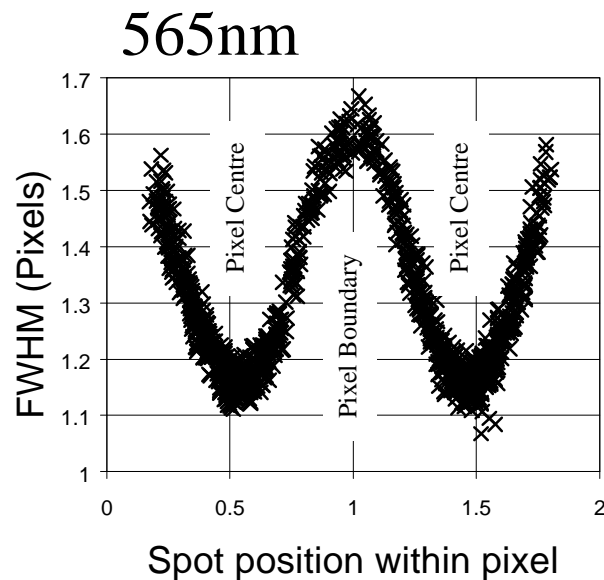
This was measured at three wavelengths using the RGO flat field projector. The exposures were sufficiently deep to reduce photon noise below 0.2% , thus revealing the intrinsic pixel-pixel sensitivity variations. A cross-hatch pattern was visible in the 390nm exposures, thought to be due to laser annealing. The sensitivity variation here was +/- 2%. At longer wavelengths this patterning disappeared and the PRNU dropped to +/- 1%.



3.4. Point Spread Function.

This was measured at two wavelengths using an optical device developed at RGO. This device used an all reflective microscope objective, pinhole and LED to project a $2\mu\text{m}$ diameter spot onto the CCD. The position of this spot could be adjusted to high precision using an X-Y translation stage. Focusing was achieved by tilting the CCD slightly with respect to the X-Y plane in which the scan head moved. The spot was then scanned down a column of the CCD during integration, thus drawing out a line image. As the spot moved first towards and then away from best focus, the width of this scan line could be seen to reach a minimum. It was thus possible to window in on a few hundred image rows close to this minimum where optimum focus was to be found. The X and Y axes of the translation stages were only approximately aligned to the rows and columns of the CCD. As the line image was scanned out down a column, there would therefore be a small component of motion along the row axis of the chip. By examining consecutive rows of the line image (close to the optimum focus position) it was then possible to measure the optical properties of the CCD at differing intra-pixel spot positions. Each line image therefore contained a great deal of information. An alternative, and very much more complex method would be to record several hundred individual spot images, stepping the position of the spot very slightly between each.

Line images were recorded at two wavelengths and the results are shown below. The CCD showed excellent spatial resolution, at least compared to Lesser thinned Loral devices.



4. Readout Noise and Readout Times

This was measured comprehensively using both photon-transfer image pairs and the more accurate Iron-55 X-ray method.

Performance of Left Hand Amplifier in Hi-Gain mode (Fe55 Method)

speed	Gain (e/ADU)	Noise (e)	Bias (ADU)
S	1.13	3.9	1900
Q	1.26	4.6	1590
T	1.56	5.2	1030
N	1.84	5.0	700

Performance of Right Hand Amplifier in Hi-Gain mode (Photon Transfer)

speed	Gain (e/ADU)	Noise (e)	Bias (ADU)
S	1.1	5	2000
Q	1.2	5	1700
T	1.5	5.6	1100
N	1.9	5.2	750

Performance of Left Hand Amplifier in Lo-Gain mode (Fe55 Method)

speed	Gain (e/ADU)	Noise (e)	Bias (ADU)
S	3.05	10.2	1900
Q	3.43	12.5	1600
T	4.16	14.3	1050
N	5.01	13.1	700

Performance of Right Hand Amplifier in Lo-Gain mode (Photon Transfer)

speed	Gain (e/ADU)	Noise (e)	Bias (ADU)
S	3.0	11.5	2020
Q	3.6	13.5	1700
T	4.4	15	1110
N	5.2	14.5	760

Binned Performance of Left Hand Amplifier in Hi-Gain Mode(Fe55 Method)

Binning	Gain (e/ADU)	Noise (e)	Bias (ADU)
2x2	1.60	5.2	1510
1x2	1.53	5.4	1870
2x1	1.60	5.6	1510

Readout Times

Speed	Full frame readout (s)
S	225
Q	180
T	165
N	120
2x2 Bin	47

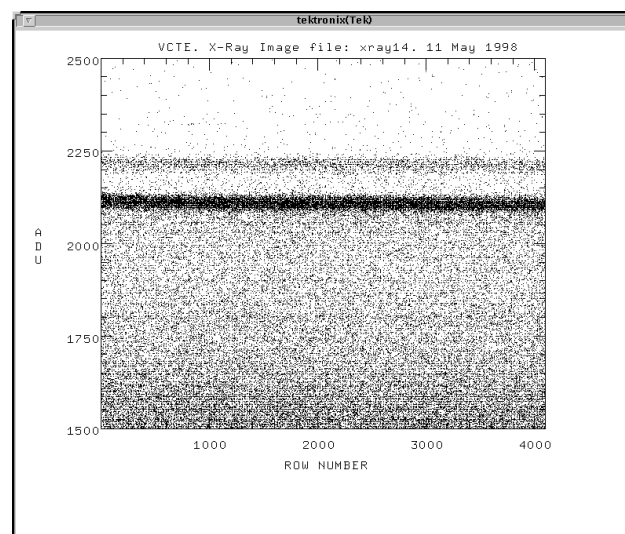
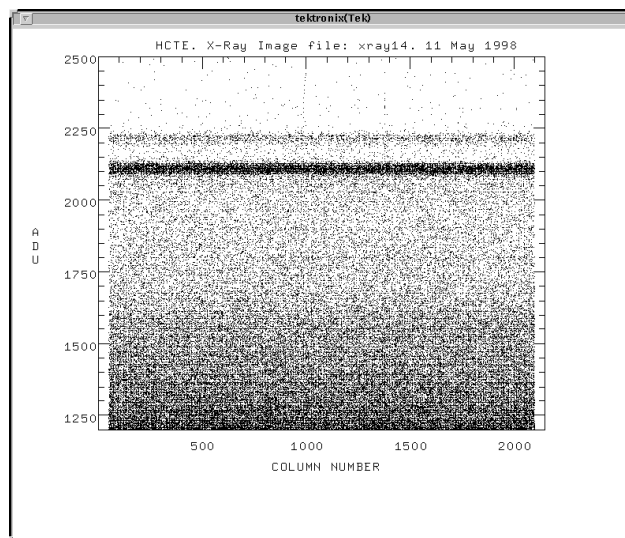
5. Charge Transfer Efficiency.

This was measured for low charge levels ($1620e^-$) using Iron-55 X-rays, and for higher levels close to full-well, using the Extended Pixel Edge Response technique. The results are tabulated below.

VCTE Fe55 ($1620e^-$)	0.999998
HCTE Fe55 ($1620e^-$)	0.999998
VCTE $200,000e^-$	0.999997
HCTE $200,000e^-$	0.9999987

Measurement temperature = -120C

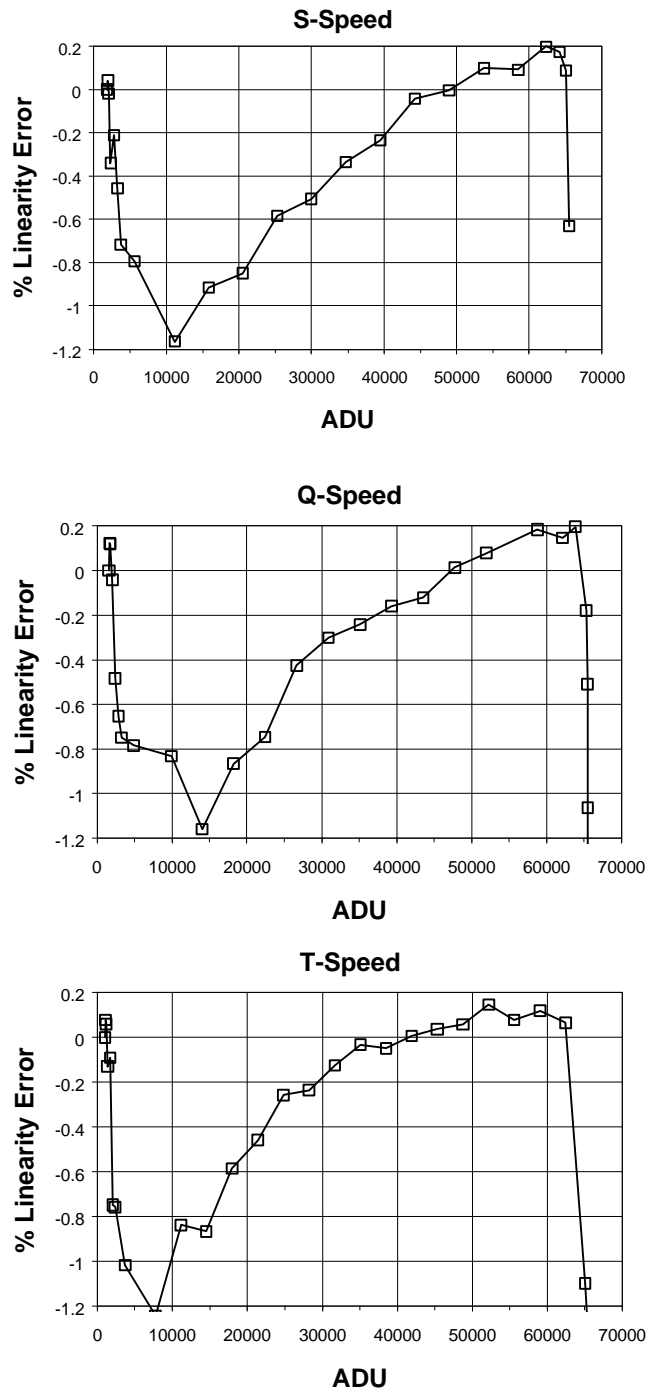
Plots of the x-ray event pixel values along the horizontal and vertical image axes are shown below.



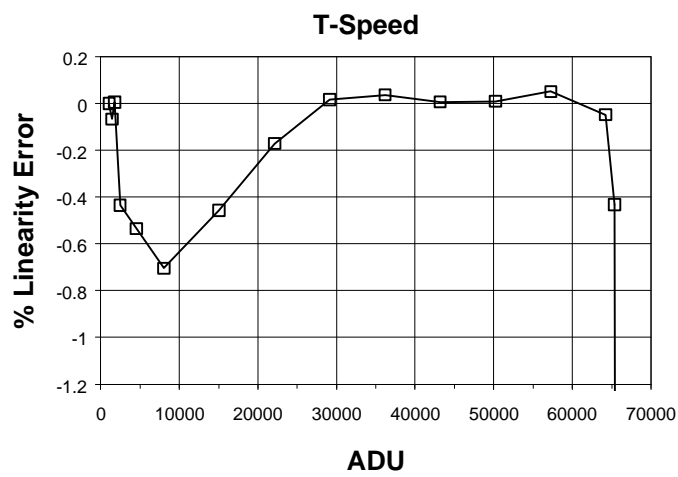
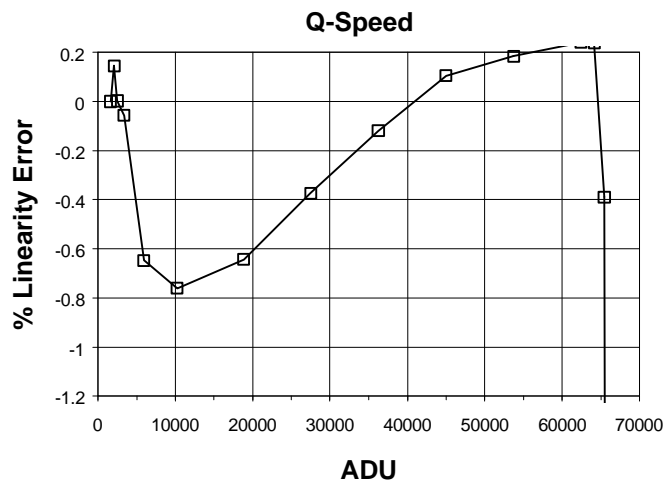
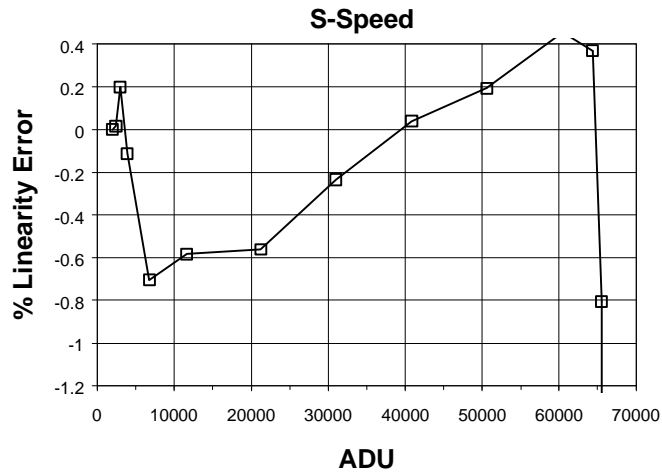
6. Linearity and Full-Well.

These characteristics were measured using a highly linear pulsed light source developed at RGO.

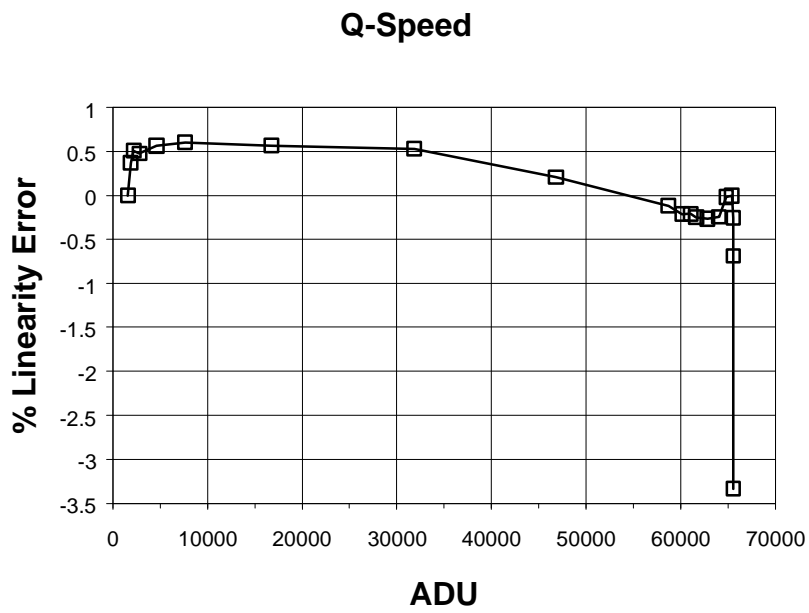
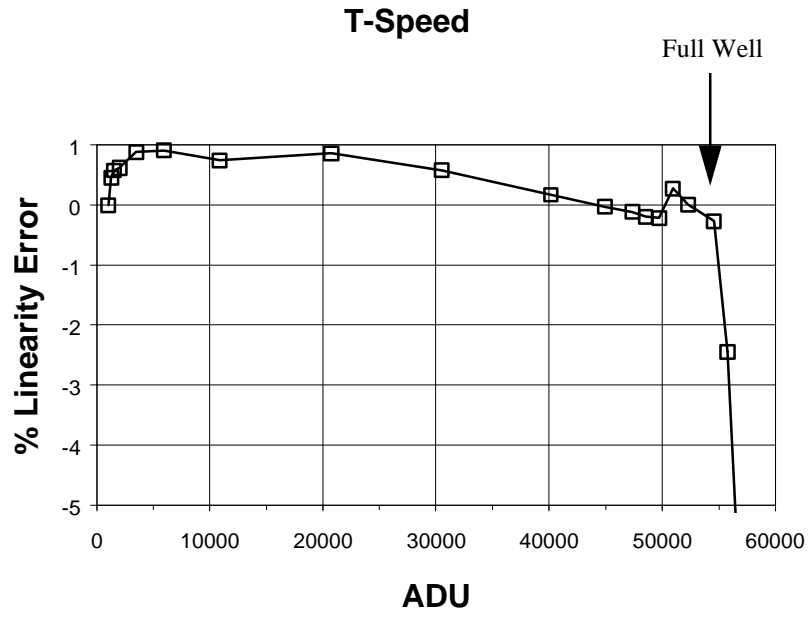
Hi-Gain Mode Linearity LEFT Hand Output



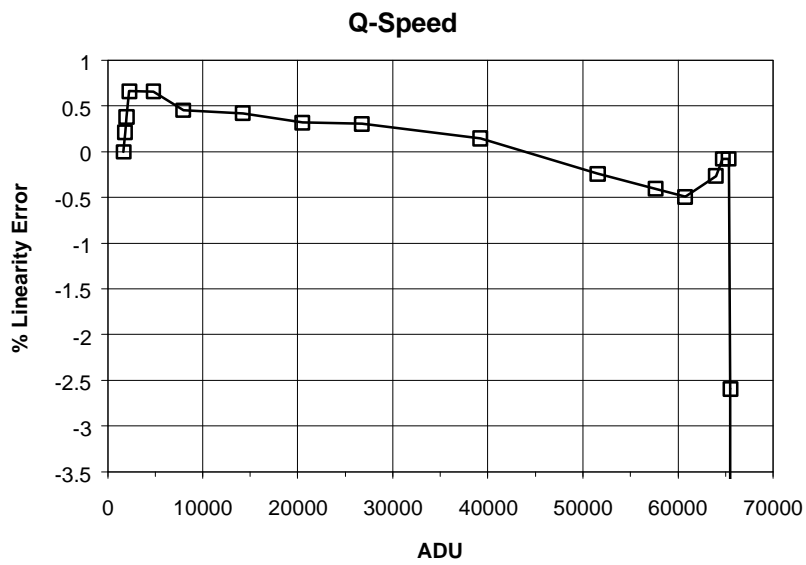
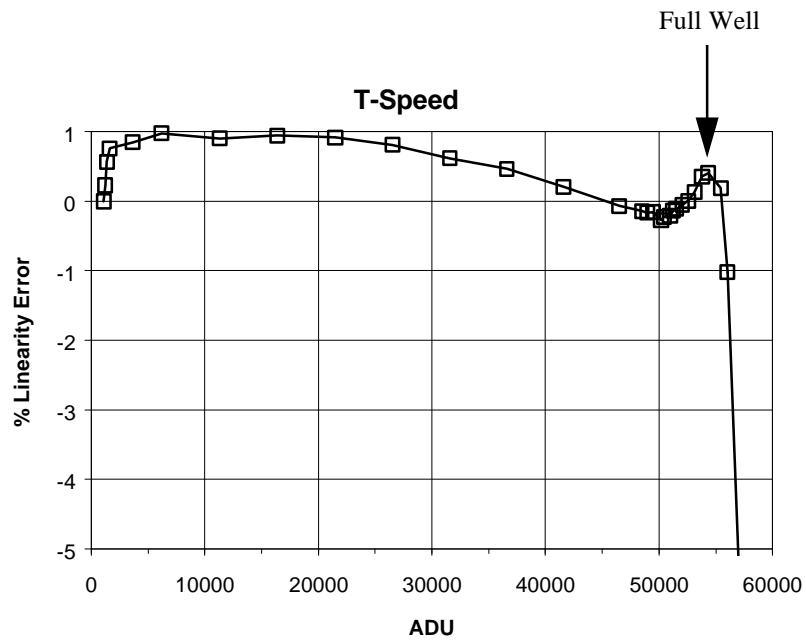
Hi-Gain Mode Linearity RIGHT Hand Output



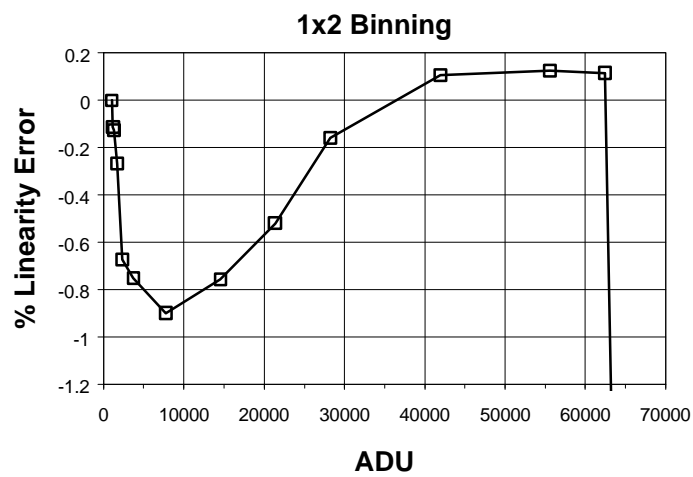
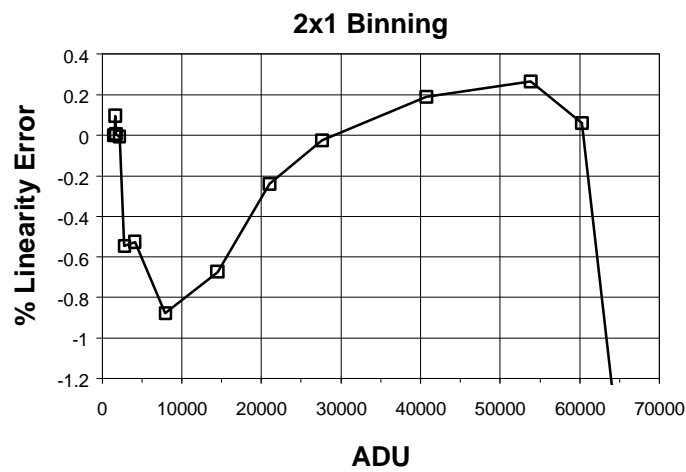
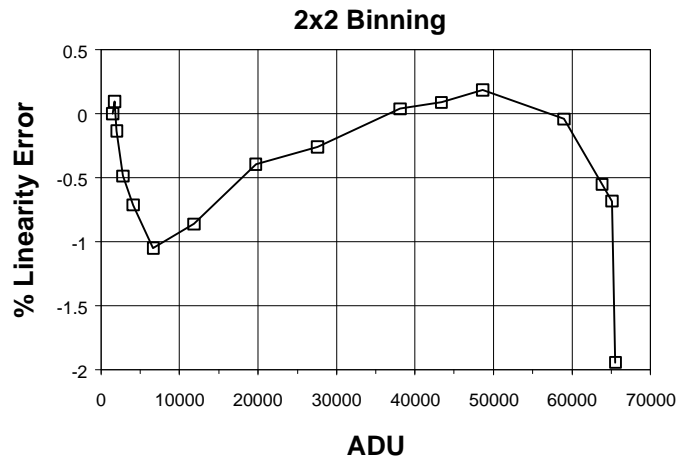
Lo-Gain Mode Linearity
LEFT Hand Output



Lo-Gain Mode Linearity RIGHT Hand Output



Binning Mode Linearity LEFT Hand Output, Hi-gain

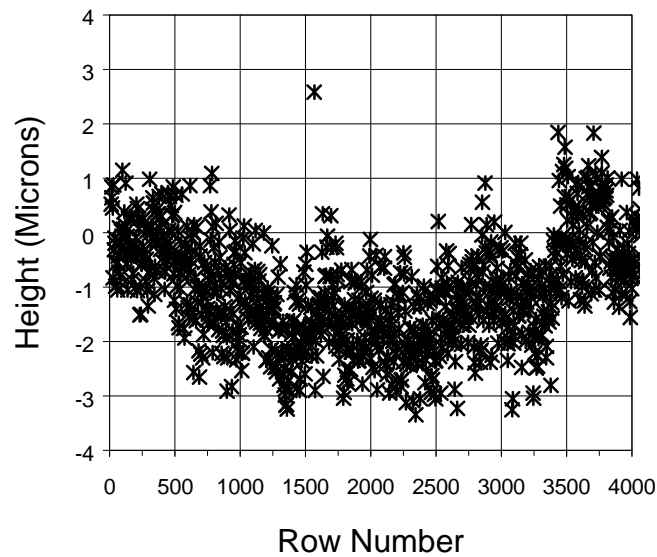


7. Mechanical Parameters.

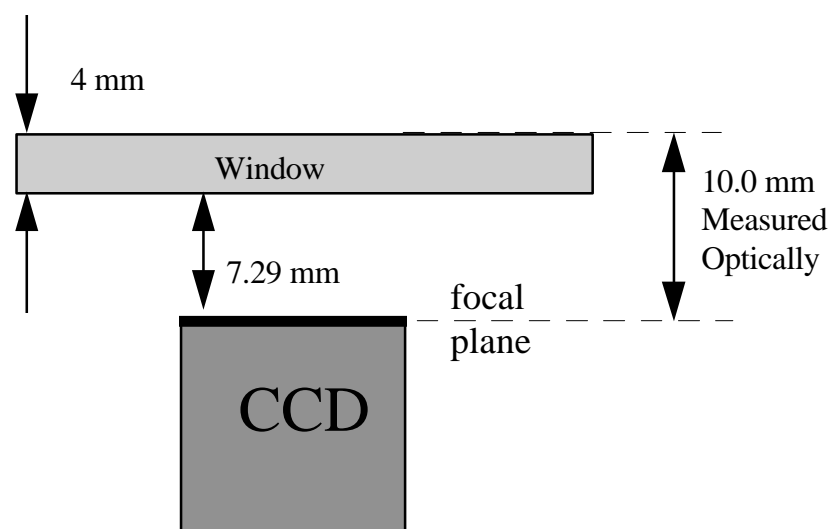
The flatness of the CCD was measured using the RGO coplanarity scanner. The distance of the CCD behind the cryostat window was measured using a travelling microscope.

7.1. Device Flatness.

The CCD was extremely flat. The following plot shows a height data from a measurement scan down the long axis of the CCD close to the central column.



7.2. Focus Distance.



Appendix A. CCD Controller Configuration Listing.

```

xterm
1 RAM-DISK 0
0 ( DEFINE CLOCKS ) SEQUENCER DEFINITIONS ( 05 May 98)
1 \ For EEV 42-80 op(L)
2 00 0 CLOCK TRACK ( TSO ) 01 1 CLOCK TRIG ( ACO )
3 02 0 CLOCK SIG-SAMP ( CSO ) 03 0 CLOCK REF-SAMP ( CRO )
4 04 1 CLOCK SIG-RST ( RSO ) 11 1 CLOCK REF-RST ( RRO )
5 17 1 CLOCK CLAMP ( CLO ) 25 0 CLOCK RSCK ( RSA )
6 ( HA1) 23 1 CLOCK 1HCK \ 23 op(L) 30 op(R)
7 ( HA2) 30 0 CLOCK 2HCK \ 30 23
8 ( HA3) 34 0 CLOCK 3HCK
9 ( HA4) 28 0 CLOCK SWCK
10 ( VA1) 24 0 CLOCK 1VCK \ lower reg. only for 42 series
11 ( VA2) 26 1 CLOCK 2VCK
12 ( VA3) 19 0 CLOCK 3VCK
13 ( VA4) 31 0 CLOCK 4VCK \ used for DG
14 ( VLA) 35 0 CLOCK RD/I \ was 0, 27/11
15 -->
<CCD7> ok

xterm
2 RAM-DISK 0
0 ( Vertical clock ) SEQUENCER DEFINITIONS ( apo 18 Dec 97)
1 0 SOR VCLOCK
2 \
3 RD/I 650 ND
4 1VCK 300 DF 300 ND \ 1VCK 300+300
5 1VCK 200 DF 300 ND \ 1VCK 300+300
6 2VCK 200 DF 300 ND \ 200+300
7 2VCK 100 DF 300 ND \ 200+300
8 3VCK 100 DF 300 ND \ 3VCK 100+300
9 3VCK 300 DF 300 ND \ 3VCK 100+300
10 2HCK 950 ND \ 650 2clks hi during v->h
11 1000 EOR \ 700, 1000
12 VCLOCK >RAM
13 -->
14
15
<CCD7> ok

xterm
3 RAM-DISK 0
0 ( Horizontal clock ) SEQUENCER ( smt 13 May 98)
1 1 SOR HCLOCK
2 RSCK 10 DF 20 ND
3 1HCK 5 DF 15 ND
4 2HCK 15 ND
5 3HCK 10 DF 15 ND
6 SWCK 10 DF 15 ND
7 35 EOR HCLOCK >RAM
8
9 15 SOR HRINT \ clock serial reg to remove glow
10 RSCK 25 ND
11 1HCK 5 DF 15 ND
12 2HCK 15 ND
13 3HCK 10 DF 15 ND
14 4VCK 1000 ND
15 1001 EOR HRINT >RAM -->
<CCD7> ok

```

```

xterm
4 RAM-DISK 0
0 ( SMT 11 May 93)
1 8 SOR ABM-CLK ( WOBBLE 1->2->1 )
2 RD/I 32000 ND
3 RSCK 32000 ND
4 1HCK 32000 ND
5 2HCK 32000 DF
6 3HCK 32000 ND
7 1VCK 4000 DF 8000 ND
8 2VCK 6000 DF 4000 ND
9 \ 3VCK 32000 ND
10 \ 4VCK 32000 ND
11 32002 EOR ABM-CLK >RAM -->
12
13
14
15
<CCD7> ok

xterm
5 RAM-DISK 0
0 ( smt 13 May 98)
1 13 SOR REM-CLK
2
3 1VCK 5000 DF
4 2VCK 5000 ND
5 3VCK 5000 DF
6 1HCK 5000 ND
7
8
9
10 5002 EOR REM-CLK >RAM
11
12
13
14
15 -->
<CCD7> ok

xterm
6 RAM-DISK 0
0 ( SMT 28 Apr 93)
1
2
3
4
5
6
7
8
9
10 BLK @ 1+ VHT BIN-BLOCK !
11 6 SOR BIN
12 3 FH LOAD
13
14
15
<CCD7> ok

```

```

xterm
7 RAM-DISK 0
0 ( Binned Block - 1 ) DECIMAL (          smt 06 May 98)
1 SEQUENCER VIA SEQUENCER FORTH ENDVIA DEFINITIONS
2
3 ; COMPILE-BIN-PIX ( xbin-factor -- ) >R BIN SOR
4   RSCK 15 ND
5
6   1HCK 5 DF I 0 DO 5 DF 15 ND 5 DF LOOP
7   2HCK 5 ND I 0 DO 15 ND 10 DF LOOP
8   3HCK 5 DF I 0 DO 5 DF 15 ND 5 DF LOOP
9
10
11   [
12
13 -->
14
15
<CCD7> ok

xterm
8 RAM-DISK 0
0 ( Binning Block - 2 ) DECIMAL (          smt 06 May 98)
1   ]
2   REF-SAMP 5 DF I 25 * DF 5 DF 40 ND
3   SWCK 5 DF I 25 * ND 55 ND 10 DF 65 ND
4   SIG-SAMP 5 DF I 25 * DF 80 DF 40 ND
5   CLAMP 5 DF I 25 * DF 5 DF 125 ND
6   SIG-RST 5 DF I 25 * DF 5 DF 125 ND
7   REF-RST 5 DF I 25 * DF 5 DF 125 ND
8   TRACK 5 DF I 25 * DF 80 DF 45 ND
9   TRIG 5 DF I 25 * DF 125 DF 5 ND
10
11 R> 25 * 135 + EOR BIN >RAM ;
12 COMPILE-BIN-PIX BIN-TEMP FORGET COMPILE-BIN-PIX
13
14
15
<CCD7> ok

xterm
9 RAM-DISK 0
0 ( Standard readout speed ) SEQUENCER (          smt 29 Apr 98)
1 2 SOR SP0 ( 8+8 us, 190s for whole frame )
2   RSCK 13 ND
3   1HCK 5 DF 15 ND
4   2HCK 15 ND
5   3HCK 5 DF 15 ND
6   REF-SAMP 25 DF 80 ND
7   SWCK 10 DF 105 ND 10 DF 110 ND
8   SIG-SAMP 135 DF 80 ND
9   TRACK 135 DF 85 ND
10  TRIG 230 DF 5 ND
11  CLAMP 25 DF 210 ND
12  SIG-RST 25 DF 210 ND
13  REF-RST 25 DF 210 ND
14
15 236 EOR SP0 >RAM -->
<CCD7> ok

```

```

xterm
10 RAM-DISK 0
0 ( QUICK readout speed ) SEQUENCER ( smt 11 May 98)
1 3 SOR SP1 ( 6+6us 160s readout )
2 RSCK 13 ND
3 1HCK 5 DF 15 ND
4 2HCK 15 ND
5 3HCK 5 DF 15 ND
6 REF-SAMP 25 DF 60 ND
7 SWCK 10 DF 85 ND 10 DF 90 ND
8 SIG-SAMP 115 DF 60 ND
9 TRACK 115 DF 65 ND
10 TRIG 190 DF 5 ND
11 CLAMP 25 DF 170 ND
12 SIG-RST 25 DF 170 ND
13 REF-RST 25 DF 170 ND
14
15 196 EOR SP1 >RAM -->
<CCD7> ok

xterm
11 RAM-DISK 0
0 ( TURBO readout speed ) SEQUENCER ( smt 11 May 98)
1 4 SOR SP2 ( 4.0 + 4.0 us CDS, 140s readout )
2 RSCK 13 ND
3 1HCK 5 DF 15 ND
4 2HCK 15 ND
5 3HCK 5 DF 15 ND
6 REF-SAMP 23 DF 40 ND
7 SWCK 5 DF 68 ND 10 DF 75 ND
8 SIG-SAMP 98 DF 40 ND
9 TRACK 98 DF 45 ND
10 TRIG 153 DF 5 ND
11 CLAMP 23 DF 135 ND
12 SIG-RST 23 DF 135 ND
13 REF-RST 23 DF 135 ND
14
15 179 EOR SP2 >RAM -->
<CCD7> ok

xterm
12 RAM-DISK 0
0 ( Nonastro readout speed ) SEQUENCER ( smt 11 May 98)
1 5 SOR SP3 ( 3 + 3 us, 93s readout )
2 RSCK 13 ND
3 1HCK 5 DF 15 ND
4 2HCK 15 ND
5 3HCK 5 DF 15 ND
6 REF-SAMP 25 DF 30 ND
7 SWCK 5 DF 60 ND 8 DF 53 ND
8 SIG-SAMP 83 DF 30 ND
9 TRACK 83 DF 35 ND
10 TRIG 123 DF 4 ND
11 CLAMP 25 DF 100 ND
12 SIG-RST 25 DF 100 ND
13 REF-RST 25 DF 100 ND
14
15 128 EOR SP3 >RAM -->
<CCD7> ok

```

```

xterm
13 RAM-DISK 0
0 ( Dummy pixel routine ) SEQUENCER ( SMT 28 Apr 93)
1 14 SOR DPIX ( ***** DUMMY PIXEL 1+1us CDS )
2 RSCK 13 ND
3 1HCK 4 DF 10 ND
4 2HCK 9 ND
5 3HCK 4 DF 10 ND
6 REF-SAMP 18 DF 10 ND
7 SWCK 5 DF 26 ND 8 DF 35 ND
8 SIG-SAMP 44 DF 10 ND
9 \ TRACK 44 DF 15 ND \ NO A/D or S/H trig for dummy
10 \ TRIG 64 DF 4 ND
11 CLAMP 15 DF 59 ND
12 SIG-RST 15 DF 59 ND
13 REF-RST 15 DF 59 ND
14
15 75 EOR DPIX >RAM -->
<CCD7> ok

xterm
14 RAM-DISK 0
0 ( Vmov w/o SR scan ) SEQUENCER ( smt 11 May 98)
1 6 SOR QUICK-CLR
2
3 1VCK 150 DF 150 ND
4 2VCK 100 DF 150 ND
5 3VCK 50 DF 150 ND
6
7
8 1HCK 400 ND
9 2HCK 400 DF
10 3HCK 400 DF
11 400 EOR
12 QUICK-CLR >RAM
13 \ V-clock charge into last row(s) to overcome low CTE...
14 -->
15
<CCD7> ok

xterm
15 RAM-DISK 0
0 ( Flash fast clear of CCD ) SEQUENCER ( apo 27 Jan 97)
1 7 SOR FLASH-CLR
2 \ RD/I 350 ND
3 1VCK 150 DF 150 ND
4 2VCK 100 DF 150 ND
5 3VCK 50 DF 150 ND
6 4VCK 400 ND \ This manipulates DD on the EEV
7 \ RSCK 400 ND
8 1HCK 400 DF
9 2HCK 400 ND
10 3HCK 400 ND
11 410 EOR
12 FLASH-CLR >RAM
13 \ 1 V-clock triplet then dump into register drain x n for EEV4x
14 -->
15
<CCD7> ok

```

```

xterm
16 RAM-DISK 0
0 ( SETUP FUNCTIONS,                               smt 11 May 98)
1 SP0          SET-SPEED0
2 SP1          SET-SPEED1
3 SP2          SET-SPEED2
4 SP3          SET-SPEED3
5 SP0          SET-SPEED4
6 BIN          SET-BIN
7 HCLK        SET-DPIX
8 HCLK        SET-HCLK
9 VCLK        SET-VCLK
10 HRINT       SET-HIDLE
11 QUICK-CLR   SET-QCLR
12 ABM-CLK     SET-AB  \ ANTI-BLOOM
13 REM-CLK     SET-RR  \ ANTI-REMNANCE
14 \           SET-CLKT
15 FLASH-CLR   SET-FCLR  -->
<CCD7> ok

xterm
17 RAM-DISK 0
0 ( Customisations for EEV42) FORTH DEFINITIONS (  smt 13 May 98)
1 : PFS  PREFLASH-SCALER ; 40 PFS ! \ 1 unit = 1.25us
2 : ENBT 0 'SILENT C! VT100 RAM-DISK 1 LIST
3   ( [ CCD5 ] CONFIG ) ;
4 : S-CLR [ VHT ] STANDARD CLEAR-SPEED ;
5 : Q-CLR [ VHT ] QUICK CLEAR-SPEED ;
6 : F-CLR [ VHT ] FLASH-CLR CLEAR-SPEED ;
7 : IOS 1 ?IS ; ; SETI -1 TIMES IOS ;
8 1 VHT 'REM-REMO C! 3000 RR-CLKS ! \ ENABLE REMNANCE
9 : HOPG 2 OPG ; ; LOPG 1 OPG ;
10 : VMOV [ SEQUENCER ] HERE 4096 3 FC HERE >FIFO ;
11 1V 2148 4128 13 NEW-TYPE EEV48 EEV48
12 0 VHT 'ANTI-BLOOM C! \ DISABLE ANTI-BLOOM
13 \ Attributes are 3 2 1 0
14 \ dump- opg- no- od-sw
15 --> \ drain sw idle
<CCD7> ok

xterm
18 RAM-DISK 0
0 ( Customisations - general) SEQUENCER ( 11 May 98)
1 5 [ ' ] PA-RES ! \ P/A res = 470ohms
2 1 1 I-OFFSET ! 7 2 I-OFFSET ! \ Set ?IS offset, for 2 heads
3 38 1 OD-ZERO ! 40 2 OD-ZERO ! \ OD Offset, For 2 heads
4 1 PHYSICAL 2064 'ZERO-AD ! 0 'SERVO-ZERO !
5 2 PHYSICAL 2064 'ZERO-AD ! 0 'SERVO-ZERO !
6 FORTH DEFINITIONS
7
8 1P -15 'SERVO-ZERO ! T-ON \ 1 unit = -0.16 degC
9 98 YEAR W!
10 NETWORK CCD7
11 : WHO? PAGE BELL CR 20 SPACES ." EEV 4280 " CR ;
12 : OPGH 0 OPG ; ; OPGL 1 OPG ;
13
14 WHO? -->
15
<CCD7> ok

```

Appendix B. Hardware Modifications to CCD Controller.

The CDS time constant was set to $4\mu\text{s}$. This was achieved by setting $C8$ and $C7 = 6.6\text{nF}$ and $R12$ and $R13 = 620\ \Omega$. $R5$ on the CDS card was set to 50K . Pre-amp resistors $R31,32,33,34$ all had 4K7 resistors soldered in parallel to reduce gain. The corresponding electronic gain of the controller is as follows :

Readout Speed	Voltage Gain
S	29.8
Q	26.9
T	21.6
N	18.3

Appendix C. Operating Voltages.

```

xterm

Chip 0 Configuration.
Virtual head number 1      Serial number is :- EEV42-80, A5500-5

0      0.00 Volts Channel 0      1      0.00 Volts Channel 0
2      0.00 Volts Channel 0      3      0.00 Volts Channel 0
4      0.00 Volts Channel 0      5      0.00 Volts Channel 0
6      0.00 Volts Channel 0      7      0.00 Volts Channel 0
V+SL  -17.70 Volts Channel 8      V-      -16.00 Volts Channel 9
V+      -6.50 Volts Channel 10     V-SL    2.40 Volts Channel 11
RD      4.00 Volts Channel 12     VSS     -9.00 Volts Channel 13
OG1    -13.00 Volts Channel 14     V++     -6.50 Volts Channel 15
R-SL   -2.00 Volts Channel 16     R-      -15.00 Volts Channel 17
R+      -5.00 Volts Channel 18     R+SL   -18.00 Volts Channel 19
ODL     7.00 Volts Channel 20     ODH     16.50 Volts Channel 21
OG2H   -12.00 Volts Channel 22     OG2L    3.00 Volts Channel 23
24      0.00 Volts Channel 0      BG      7.00 Volts Channel 25
DMP     5.00 Volts Channel 26     H++     -2.00 Volts Channel 27
H+      -5.00 Volts Channel 28     H-      -14.00 Volts Channel 29
H-SL   -2.00 Volts Channel 30     H+SL   -18.00 Volts Channel 31

<CCD7> ok

```